



(19)

Generated Document.

(11) Publication number: **05062911 A**

PATENT ABSTRACTS OF JAPAN

(21) Application number: **03223234**

(51) Intl. Cl.: **H01L 21/205 H01S 3/18**

(22) Application date: **04.09.91**

(30) Priority:

(43) Date of application publication: **12.03.93**

(84) Designated contracting states:

(71) Applicant: **FUJITSU LTD**

(72) Inventor: **NAKAI KENYA**

(74) Representative:

(54) MANUFACTURE OF SEMICONDUCTOR SUPERLATTICE

(57) Abstract:

PURPOSE: To form a Ge layer and an Si layer or a Ge-Si layer and an Si layer on an Si substrate, and also to put a hetero-epitaxial growth method, in which excellent crystal quality and high growth speed can be obtained, into practical use.

CONSTITUTION: The title semiconductor superlattice

manufacturing method is the method with which a Ge layer and an Si layer or Ge-Si layer and an Si layer are epitaxially grown on an Si substrate by conducting a depressed CVD method under the atmosphere containing oxidizing impurity gas of 1000ppb or lower using GeH₄ and trisilane (Si₃H₈) as raw gas and also using H₂ or inert gas as carrier gas.

COPYRIGHT: (C)1993,JPO&Japio



